

Attorney Docket #10961260-3

Amendments to the Claims

This list of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously presented) A semiconductor isolation structure comprising:
 - a substrate, the substrate comprising a surface;
 - a first device and a second device formed within the substrate;
 - an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:
 - a single deep region which extends into the substrate, the deep region comprising a deep region cross-sectional area, the deep region abutting only the substrate and a single shallow region;
 - [a] the single shallow region [which extends] extending to the surface of the substrate, the shallow region comprising:
 - a protective outer wall adjacent to the substrate and extending to the surface of the substrate;
 - an inner sealing wall located exclusively within the shallow region and adjacent to the protective outer wall, extending to the surface of the substrate[:]; and
 - the shallow region having a shallow region cross-sectional area;
 - wherein the deep region cross-sectional area is greater than the shallow region cross-sectional area, the deep region abutting only a single shallow region.
2. (Original) The semiconductor isolation structure as recited in claim 1, wherein the isolation region comprises an oxide.
3. (canceled)

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4. (Previously presented) The semiconductor isolation structure as recited in claim 1, wherein the protective outer wall comprises a layer of oxide.

5. (Previously presented) A semiconductor isolation structure comprising:

a substrate, the substrate comprising a surface;

a first device and a second device formed within the substrate;

an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:

a single deep region which extends into the substrate, the deep region comprising an oxide, the deep region abutting only the substrate and a single shallow region;

[a] the single shallow region [which extends] extending to the surface of the substrate, the shallow region comprising:

a protective outer wall adjacent to the substrate and extending to the surface of the substrate,

an inner sealing wall located exclusively within the shallow region and adjacent to the protective outer wall, extending to the surface of the substrate.

6. (Previously presented) The semiconductor isolation structure of claim 5, in which the protective outer wall comprises an oxide and the inner sealing wall comprises a nitride.

Claims 7-9 (canceled)